



**Spec No.: DS30-2001-344**Effective Date: 11/27/2001

Revision: -

**LITE-ON DCC** 

**RELEASE** 

BNS-OD-FC001/A4

## Property of Lite-On Only

#### **FEATURES**

- \*1.2 inch (30.5 mm) DIGIT HEIGHT.
- \*CONTINUOUS UNIFORM SEGMENTS
- \*LOW POWER REQUIREMENT.
- \*EXCELLENT CHARACTERS APPEARANCE.
- \*HIGH BRIGHTNESS & HIGH CONTRAST.
- \*WIDE VIEWING ANGLE.
- \* SOLID STATE RELIABILITY.
- \*CATEGORIZED FOR LUMINOUS INTENSITY.

#### **DESCRIPTION**

The LTP-12802KD is a 1.2 inch (30.5 mm) digit height single digit 16-segment alphanumeric display. This device utilizes AlInGaP Hyper Red LED chips, which are made from AlInGaP on a non-transparent GaAs substrate, and has a black face and white segments.

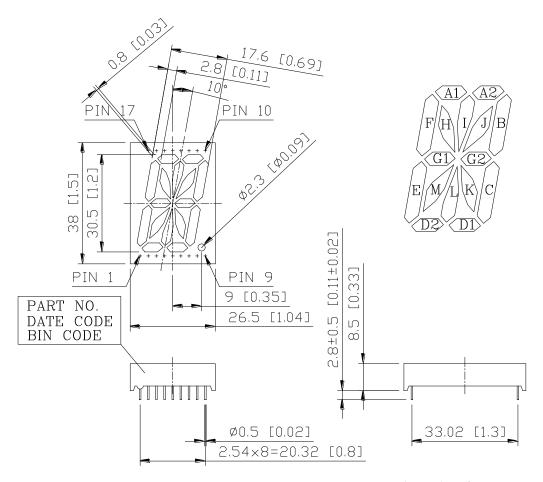
#### **DEVICE**

PART NO.	DESCRIPTION		
AlInGaP Hyper Red	Common Anode		
LTP-12802KD	Rt. Hand Decimal		

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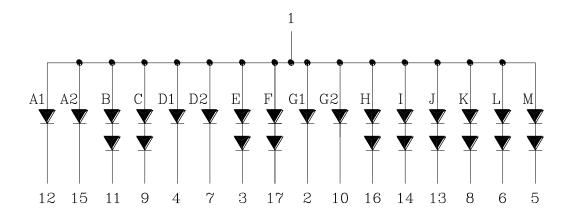
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### PACKAGE DIMENSIONS



NOTES: All dimensions are in millimeters. Tolerances are  $\pm$  0.25-mm (0.01") unless otherwise noted.

## INTERNAL CIRCUIT DIAGRAM



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**Property of Lite-On Only** 

## PIN CONNECTION

No.	CONNECTION
1	COMMON ANODE
2	CATHODE G1
3	CATHODE E
4	CATHODE D1
5	CATHODE M
6	CATHODE L
7	CATHODE D2
8	CATHODE K
9	CATHODE C
10	CATHODE G2
11	CATHODE B
12	CATHODE A1
13	CATHODE J
14	CATHODE I
15	CATHODE A2
16	CATHODE H
17	CATHODE F

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### ABSOLUTE MAXIMUM RATING AT Ta=25°C

PARAMETER	MAXIMUM RATING	UNIT			
Power Dissipation Per Segment	70 (134)	mW			
Peak Forward Current Per Segment	00	1			
(1/10 Duty Cycle, 1.0ms Pulse Width)	90	mA			
Continuous Forward Current Per Segment	25 (24)	mA			
Derating Linear From 25 <sup>o</sup> C Per Segment	0.33 (0.31)	mA/ <sup>0</sup> C			
Reverse Voltage Per Segment	5 (10)	V			
Operating Temperature Range	$-35^{\circ}$ C to $+85^{\circ}$ C				
Storage Temperature Range	$-35^{\circ}$ C to $+85^{\circ}$ C				
Solder Temperature: max 260°C for max 3sec at 1.6mm[1/16inch] below seating plane.					

## ELECTRICAL / OPTICAL CHARACTERISTICS AT Ta=25°C

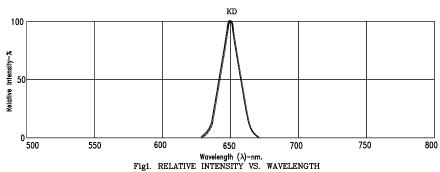
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
	Iv		27.3		,	I=20mA
Average Luminous Intensity			(46.8)		mcd	
Peak Emission Wavelength	λр		650		nm	I <sub>F</sub> =20mA
Spectral Line Half-Width	Δλ		20		nm	I <sub>F</sub> =20mA
Dominant Wavelength	λd		639		nm	I <sub>F</sub> =20mA
Forward Voltage Per Segment	VF		2.1	2.6	V	I <sub>F</sub> =20mA
			(4.2)	(5.2)		
Reverse Current Per Segment	IR			100	μΑ	V <sub>R</sub> =5V (10V)
Luminous Intensity Matching Ratio	Iv-m			2:1		I <sub>F</sub> =20mA

Note: Luminous intensity is measured with a light sensor and filter combination that approximates the CIE (Commision Internationale De L'Eclairage) eve-response curve.

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### TYPICAL ELECTRICAL / OPTICAL CHARACTERISTIC CURVES

(25°C Ambient Temperature Unless Otherwise Noted)



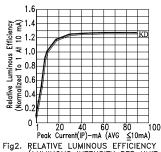
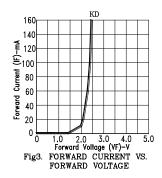
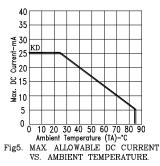


Fig2. RELATIVE LUMINOUS EFFICIENCY (LUMINOUS INTENSITY PER UNIT CURRENT) VS. PEAK CURRENT



Relative Lur (Normalized 1.2 Forward Current (IF)-mA
Fig4. RELATIVE LUMINOUS INTENSITY

VS. FORWARD CURRENT



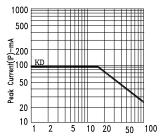


Fig6. MAX. PEAK CURRENT VS. DUTY CYCLE % (REFRESH RATE 1KHz)

NOTE : KD=AlInGaP HYPER RED

Note: Per chip dice.

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